

at least a second electrode or an insulation layer formed on the second major surface opposite to said first major surface; and

at least a conductive member for connecting said first electrode with said second electrode or said insulation layer, said conductive member being formed along the outer circumference of at least a side of said semiconductor chip,

wherein each of said conductive members is comprised of a conductive layer formed on the surface of said semiconductor chip extending from said first electrode to said second electrode or said insulation layer such that at least a portion of said conductive layer contacts said surface.

6. A semiconductor device comprising:

a plurality of semiconductor device units, each of said semiconductor device units including:

a semiconductor chip;
at least a first electrode formed on the first major surface of said semiconductor chip,
at least a second electrode or an insulation layer formed on the second major surface opposite to said first major surface; and

at least a conductive member for connecting said first electrode with said second electrode or said insulation layer, said conductive member being formed along the outer circumference of at least a side of said semiconductor chip;

wherein said semiconductor device units are stacked on each other,
wherein a first chip has a first conducting pattern extended from said first electrode, a second chip has a second conducting pattern extended from said second electrode or insulation

Cont'd
D2

layer, and a bump is provided between said first conducting pattern and said second conducting pattern, which face to each other, for electrically connecting said two conducting patterns.

9. A semiconductor device comprising:

a plurality of semiconductor device units, each of said semiconductor device units including:

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- a semiconductor chip;
- at least a first electrode formed on the first major surface of said semiconductor chip,
- at least a second electrode or an insulation layer formed on the second major surface opposite to said first major surface; and

- at least a conductive member for connecting said first electrode with said second electrode or said insulation layer, said conductive member being formed along the outer circumference of at least a side of said semiconductor chip;

- wherein said semiconductor device units are stacked on each other, and said conductive members are connected to each other,

- wherein each of said conductive members is comprised of a conductive layer formed on the surface of said semiconductor chip extending from said first electrode to said second electrode or said insulation layer such that at least a portion of said conductive layer contacts said surface.

D4

13. A semiconductor device comprising:

- a plurality of semiconductor device units, each of said semiconductor device units including:

cont
D4

a semiconductor chip;
at least a first electrode formed on the first major surface of said semiconductor chip,
at least a second electrode or an insulation layer formed on the second major surface
opposite to said first major surface; and
at least a conductive member for connecting said first electrode with said second
electrode or said insulation layer, said conductive member being formed along the outer
circumference of at least a side of said semiconductor chip;
a packaging board for mounting said plurality of semiconductor device units;
wherein said semiconductor device units are placed on said packaging board so as to have
a predetermined angle to said packaging board, and said conductive members of said
semiconductor device units are connected to said packaging board,
wherein each of said conductive members is comprised of conductive layer formed on the
surface of said semiconductor chip extending from said first electrode to said second electrode or
said insulation layer such that at least a portion of said conductive layer contacts said surface.

14. A semiconductor device comprising:

a plurality of semiconductor chips each having electrodes formed on the major surface
thereof, and
a plurality of spacer members each having a conductive pattern on the surface thereof,
wherein each of said plurality of semiconductor chips has first and second opposing side
surfaces arranged adjacent to first and second spacer members of said plurality of spacer
members, respectively;

Cont'd
D4 wherein said semiconductor chips and said spacer members are stacked alternately such that said electrodes of said semiconductor chips directly contact corresponding conductive patterns at a portion of the corresponding conductive patterns formed on the surface of the spacer member and are electrically connected to said conductive patterns of said spacer members, and said conductive patterns of said spacer members are electrically connected to each other.

SEE APPENDIX FOR CHANGES MADE TO CLAIMS

Please add the following new claims:

D5 --17. The semiconductor device according to claim 3, wherein said conductive member includes a first conductive end which contacts said first electrode, and a second conductive end which contacts said second electrode or said insulation layer.

18. The semiconductor device according to claim 8, wherein said conductive member includes a first conductive end which contacts said first electrode, and a second conductive end which contacts said second electrode or said insulation layer.

19. The semiconductor device according to claim 12, wherein said conductive member includes a first conductive end which contacts said first electrode, and a second conductive end which contacts said second electrode or said insulation layer.--